# ...nce Molding Series Regulator IC SI-3000KM series

SANKEN ELECTRIC CO., LTD.

# --- Contents ---

1. Genera	al Description		
	1-1 Features		3
	1-2 Application		3
	1-3 Type		3
2. Specifi	ication		
	2-1 Package Information		4
	2-2 Ratings		5
	2-3 Circuit Diagram	4	10
3. Operat	ional Description		
	3-1 Voltage Control		12
	3-2 Overcurrent Protection		12
	3-3 Thermal Shutdown		13
	96 60		
4. Cautio	ns		
	4-1 External Components		14
	4-2 Pattern Design Notes		15
5. Applic	ations		
	5-1 Output ON/OFF Control		16
K	5-2 Thermal Design		16
6. Typica	al Characteristics		
	6-1 SI-3012KM		18
<b>3</b>	6-2 SI-3010KM		20

# 1. General Description

The SI-3000KM is a series regulator IC using a hyposaturation type PNP bipolar transistor in the power section and it can be used with the low difference of input/output voltages. It is provided with an ON / OFF terminal which operates in Active High mode and the current consumption of circuits at OFF time is zero.

### • 1-1 Features

Output current 1A

Output current is 1A at maximum with the outline of TO-252-5L.

- Hyposaturation (Vdif = 0.6 Vmax / Io = 1A)

It can be designed with low difference of input/output voltages.

- ON/OFF function

The ON/OFF terminal which can be directly controlled by TLL logic signals is provided

- Low current consumption

Current consumption of circuits at OFF time is zero.

Quiescent Current at no load is 600µA at maximum.

- High ripple attenuation ratio

75dB: F = 100 - 120kHz at Vo = 5V

- Built-in Overcurrent protection / Thermal shutdown

The automatic restoration and Foldback type overcurrent protection and Thermal shutdown circuit are built in.

### • 1-2 Application

For on-board local power supplies, power supplies for OA equipment, stabilization of secondary output voltage of regulator and power supply for communication equipment

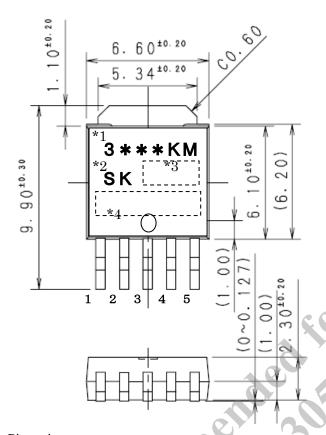
### ● 1-3 Type

- Type: Semiconductor integrated circuits (monolithic IC)
- Structure: Resin molding type (transfer molding)

# 2. Specification

Unit: mm

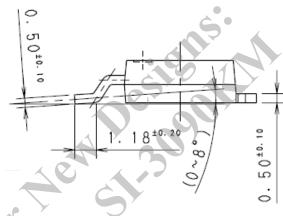
### **2-1 Package Information**



Pin assignment

- 1. Vc
- 2. VIN
- 3. GND
- 4. Vout
- 5. Sense (or ADJ terminal for SI-3010KM/SI-3012KM)

The stem part has same potential as No. 3 pin (GND).



Marking Method

\*1:Product Name

\*2:Logo Mark

\*3:Lot Number

1st letter: The last digit of year

2nd letter : Month

1 to 9 for Jan. to Sept., O for Oct.

N for Nov. D for Dec.

3rd letter: day

1 to 9day: for "1" to "9"

10 to 31day : for "A" to" Z"

(But, "B", "I", "O", "Q" is removed.

\*4:Administer number (Seven

digit)

Product mass: about 0.33 g

### • 2-2 Ratings

2-2-1 Absolute Maximum Ratings

$T_{\alpha}$	_	25	0	
1 a	=	2.7	- (	٠.

		Rat				
Parameter	Symbol	SI-3012KM/3025KM	SI-3010KM/2050KM	Units		
		/3033KM	/3090KM/3120KM			
DC Input Voltage	$V_{ m IN}$	17	35* <sup>1</sup>	V		
Output Control Terminal	17	$ m V_{C}$ $ m V_{IN}$		V		
Voltage	$V_{\rm C}$	V	V			
DC Output Current	Io	1	A			
Power Dissipation	PD*2		W			
Junction Temperature	Tj	-30 rc	-30 ro +125			
Storage Temperature	Tstg	-30 to	+125	°C		
Thermal Resistance	Oi o	0	5	°C/W		
(Junction to Air)	θj-a	9	3	CXW		
Thermal Resistance	Qi o			°C/W		
(Junction to Case)	θј-с			C/ W		

<sup>\*1:</sup> A built-in input-overvoltage-protection circuit shuts down the output voltage at the Input Overvoltage Shutdown Voltage of the electrical characteristics.

### 2-2-2 Recommended Conditions

							_/				
D .	0 1 1	Ratings									
Parameter	Symbol	SI-3012KM	SI-3025KM	SI-3033KM	SI-3010KM	SI-3050KM	SI-3090KM	SI-3120KM	Units		
Input	* 7	2.4*2 to	2.4*2 to	*2 to 6.0*1	2.4*2 to	2.4*2 to	*2 to 20*1	*2 to 25*1	***		
Voltage	$V_{IN}$	6.0*1	5.0*1		27*1	17*1			V		
Output						, "					
Current	Io	0 to 1.0							A		
Operational			V., (1)								
Ambient	Top		-30 to 85								
Temperature											
Junction Temperature in	Tj		-20 to 100								
Operation											

<sup>\*1:</sup>  $V_{IN}$  (max) and Io (max) are restricted by the relationship  $P_D$  (max) =  $(V_{IN} - V_O) \times I_O$ .

40t 130751

<sup>\*2:</sup> When mounted on glass-epoxy board of 900mm<sup>2</sup> (copper laminate area 4.3%).

<sup>\*2:</sup> Refer to the Dropout Voltage parameter.

2-2-3 Electrical Characteristics(1) (SI-3012KM,SI-3025KM,SI-3033KM) Ta = 25°C

2-2-3 EIG	cui cai c	II Characteristics(1) (SI-3012KM,SI-3025KM,SI-3033KM) $1a = 25$								, С	
						Ratings					
Parameter	Symbol	SI-3012	SI-3012KM(Vo adjustable)			SI-3025KM			SI-3033KM		
		min	typ	max	min	typ	max	min	typ	max	
Input	V <sub>IN</sub>	2.4*1			*1			*1	7.1		V
Voltage	- 114										
Output	V <sub>o</sub>	(1.24)	(1.28)	(1.32)	2.45	2.5	2.55	3.234	3.300	3.366	
Voltage	(V <sub>adi</sub> ) Conditio			, ,	2.13	2.5	2.33	3.234 3.300 3.300			V
Settings	ns	V <sub>IN</sub> =	3.3V,Io=10	)mA	V <sub>IN</sub> :	=3.3V,Io=10	)mA	$V_{IN}$			
8	Δ			15			15			15	
Line	V <sub>OLINE</sub> Conditio	377	INI 224- 01				13			15	mV
Regulation	ns		N=3.3 to 8'		V <sub>IN</sub> :	=3.3V,Io=10	)mA	V <sub>IN</sub> =	111 4		
	Δ	10=1	0mA(Vo=2				l				
Load	$V_{OLOAD}$			40			40			40	
Regulation	Conditio ns	$V_{IN}$	=3.3V, Io=0	) to	V <sub>IN</sub> =	3.3V, Io=0	to 1 A	V <sub>INE</sub>	5V, Io=0 t	$Q_{1A}$ $\downarrow 1$	mV
		1	A(Vo=2.5V	)	* IIN		10 171	, IIV	3 7, 10, 0 1		
	V <sub>DIFI</sub>			0.4			0.4		0,	0.4	<b>*</b>
Dropout	Conditio ns	Io=0	).5A(Vo=2.	5V)		Io=0.5A			Io=0.5A		***
Voltage	$V_{\mathrm{DIF2}}$			0.6			0.6	<b>Y</b>		0.6	V
	Conditio ns	Io=	1A(Vo=2.5	V)		Io=1A	3	Io=1A			
Quiescent	Iq		`	350		,	350			350	
Circuit	Conditio	V <sub>IN</sub> =3.	3V.Io=0A.V						_	I.	μA
Current	ns	VIIN OIL	$V_{IN}$ =3.3V, $Io$ =0A, $V_C$ =2V, R2=24k $\Omega$		$V_{IN}=3.3V,Io=0A,V_{C}=2V$		$V_{IN}=5V$ , $Io=0A$ , $V_C=2V$			,	
Circuit	Iq(OFF)			1			1			1	
Current at	Conditio				C.			2		I.	μΑ
Output OFF	ns	$V_{IN}$	$=3.3V,V_{C}=$	0V	VII	$V=3.3V,V_C=$	:0V	$V_{I}$	$N=5V, V_C=0$	OV	ļ
Temperature	∠Vo/		±0.3			±0.3			±0.3		
Coefficient	∠Ta		=0.5			0.5			_ 0.3		
of Output	Conditio	Ti-0 to	100°C(Vo:	-2 5V)	Tj=0 to 100℃			Tj=0 to 100°C			mV/°C
Voltage	ns	13=0 to	Tj=0 to $100^{\circ}$ C(Vo=2.5V)		1j=0 to 100 C		1,-0 10 100 C				
Ripple	R <sub>REJ</sub>		55			55			55		
Rejection	Conditio	V <sub>IN</sub> :	=3.3V,f=10	0 to		•	l			ı	dB
	ns		0Hz,Vo=2.5		V <sub>IN</sub> =3.3V,f=100 to 120Hz		$V_{IN}=5V, f=100 \text{ to } 120Hz$				
Overcurrent	$I_{S1}$	1.1	0112, (0 310	G	1.1			1.1			
Protection	*S1	- 111			1.1			1.1		l	
Starting	Conditio		V <sub>IN</sub> =3.3V			V <sub>IN</sub> =3.3V			V <sub>IN</sub> =5V		A
Current*2	ns		111-3:51			VIN-3.5 V			* IN-5 *		
Control Voltage			1								
(Output ON)*3	V <sub>C</sub> ,IH	2.2			2.2			2.2			
Control			7								V
Voltage (Output Vc. OFF)	V <sub>C</sub> ,IL			0.8			0.8			0.8	
Termin Control	I <sub>C</sub> ,IH			40			40			40	
(Output ON)	Conditio		V <sub>C</sub> =2V			V <sub>C</sub> =2V			V <sub>C</sub> =2V		
Control	ns	J _ 1									μΑ
Current (Output	I <sub>C</sub> ,IL Conditio	-5	0		-5	0		-5	0		
OFF)	ns		$V_C=0V$			$V_C=0V$			$V_C=0V$		

<sup>\*1:</sup> Refer to the clause of a difference in input and output voltage.

### Attention ...

As PD= $(V_{IN}-V_0)\times I_0$ ,  $V_{IN}(MAX)$  and  $I_0(MAX)$  must be referred to the data of P17, copper area vs power dissipation upon actual applications.

<sup>\*2:</sup> Is1 is specified at the 5% drop point of output voltage Vo on the condition that VIN = overcurrent protection starting current, Io = 10mA.

<sup>\*3:</sup> Output is OFF when the output control terminal Vc is open. Each input level is equivalent to LS-TTL level. Therefore, the device can be driven directly by LS-TTLs.

2-2-3 Electrical Characteristics(2) (SI-3010KM,SI-3050KM,SI-3090KM) Ta = 25°C

2-2-3 Elec	Juicai (	Inaracte	HSucs(2	(51-3	outukivi,	21-2020K	M,S1-30	9UKM)		1a = 25	
			Ratings								
Parameter	Symbol	SI-3010	KM(Vo adj	ustable)		SI-3050KM			SI-3090KM		
		min	typ	max	min	typ	max	min	typ	max	
Input	$V_{IN}$	2.4*1			*1			*1			V
Voltage											
Output	$V_{O \text{ or}}$ $(V_{adi})$	(0.98)	(1.00)	(1.02)	4.90	5.00	5.10	8.82	9.00	9.18	
Voltage	Conditio	**	<b></b>			<b>5</b> 777 40					V
Settings	ns	V <sub>IN</sub>	=7V,Io=10	mA	VII	<sub>N</sub> =7V,Io=10	mA	V <sub>IN</sub> :	=11V,Io=10	)mA	
	∠ V <sub>OLINE</sub>			30			75			54	
Line	Conditio	V	IN=6 to 11	V.		II.	II.		ı	À.	mV
Regulation	ns		10mA(Vo=		V <sub>IN</sub> =6	6 to 11V,Io=	:10mA	V <sub>IN</sub> =10			
Ti	Δ			75			40			40	
Load	V <sub>OLOAD</sub> Conditio						<u> </u>				mV
Regulation	ns	$V_{IN}=7V$ ,	Io=0 to 1A	(Vo=5V)	V <sub>IN</sub> :	=7V, Io=0 to		V <sub>IN</sub> =	11V, Io=0		
	V <sub>DIF1</sub>			0.3			0.3			0.3	
Dropout	Conditio ns	Io=	=0.5A(Vo=5	(V)		Io=0.5A			Io=0.5A		V
Voltage	$V_{\rm DIF2}$			0.6			0.6			0.6	V
	Conditio ns	Io	=1A(Vo=5	V)		Io=1A			Io=1A	,	
Quiescent	Iq			600			600			600	
Circuit	Conditio	V <sub>IN</sub> =7	V,Io=0A,V	L					1		μΑ
Current	ns		R2=10kΩ	C,	$V_{IN}=7V$ , $Io=0A$ , $V_C=2V$			V <sub>IN</sub> =11,Io=0A,V <sub>C</sub> =2V			μΛ
Circuit	Iq(OFF)		-	1			7 1	5		1	
Current at	Conditio								ı	ı	μΑ
Output OFF	ns	$V_{I}$	$_{\rm IN}=7V, V_{\rm C}=0$	)V	$V_{IN}=7V, V_C=0V$			$V_{IN}=11V, V_{C}=0V$			· 
Temperature	∠Vo/		±0.5			±0.5			±1.0		
Coefficient	∠Ta		_ 0.5			= 0.5			_1.0		
of Output	Conditio	Ti=0 1	to 100℃(Vo	Vo=5V) Tj=0 to 100℃			C.	Tj=0 to 100°C			mV/°C
Voltage	ns	1,-0	10000(11	3_3 ( )	1,50 100 0			-			
Ripple	R <sub>REJ</sub>		75			75			68		
Rejection	Conditio	V	N=7V,f=100	to		3					dB
	ns		20Hz,Vo=5		$V_{IN}=7V, f=100 \text{ to } 120Hz$		V <sub>IN</sub> =11V,f=100 to 120Hz				
Overcurrent	$I_{S1}$	1.1			1.1			1.1			
Protection	31	./		6	7		III		ı	ı	
Starting	Conditio ns		V <sub>IN</sub> =7V	· Y		$V_{IN}=7V$		$V_{IN}=11V$			A
Current*2	11.5			2							
Control Voltage (Output	V <sub>c</sub> ,IH	2.0	.1		2.0			2.0			
ON)*3 Control Voltage											V
V <sub>C</sub> (Output OFF)	V <sub>C</sub> ,IIL		) y	0.8			0.8			0.8	
Termin Control	I <sub>C</sub> ,IH			40			40			40	
(Output ON)	Conditio ns		$V_C=2V$			$V_C=2V$			$V_C=2V$		
Control Current	I <sub>C</sub> ,IL	-5	0		-5	0		-5	0		μΑ
(Output OFF)	Conditio		V <sub>C</sub> =0V	•		V <sub>C</sub> =0V	•		V <sub>C</sub> =0V		
Input	ns V <sub>OVP</sub>	33	, ( -0 ,		26	, , , , ,		30	, C-0 ,		
Overvoltage		33		1	∠0	1	1	30	l	l	V
Shutdown	Conditio ns		Io=10mA			Io=10mA			Io=10mA		V
Voltage					•						

<sup>\*1:</sup> Refer to the clause of a difference in input and output voltage.

Attention ...

SI-3010KM,SI-3050KM,SI-3090KM cannot be used in the following applications because the built-in foldback-type overcurrent protection may cause errors during start-up stage;

<sup>\*2:</sup> Is1 is specified at the 5% drop point of output voltage Vo on the condition that VIN = overcurrent protection starting current, Io = 10mA.

<sup>\*3:</sup> Output is OFF when the output control terminal Vc is open. Each input level is equivalent to LS-TTL level. Therefore, the device can be driven directly by LS-TTLs.

(1) Constant current load (2) Positive and negative power supply (3) Series-connected power supply (4) Vo adjustment by raising ground voltage

As PD= $(V_{IN}-V_0)\times I_0$ ,  $V_{IN}(MAX)$  and  $I_0(MAX)$  must be referred to the data of P17, copper area vs power dissipation upon actual applications.

2-2-3 Electrical Characteristics(3) (SI-3120KM)

 $Ta = 25^{\circ}C$ 

2-2-3 Elec	ziricai (	naracte	ristics(3	<u>(SI-3</u>	120KM)	$Ta = 25^{\circ}C$
		Ratings		Units		
Parameter	Symbol	SI-3120KM				
		min	typ	max		
Input	V <sub>IN</sub>	*1			V	
Voltage	- 114					
Output	V <sub>O or</sub>	11.76	12.00	12.24		
Voltage	(V <sub>adj</sub> ) Conditio				V	Ġ.
Settings	ns	$V_{II}$	$_{N}$ =7V,Io=10:	mA		Designs of
				72		
Line	V <sub>OLINE</sub> Conditio	V	IN=13 to 18		mV	
Regulation	ns	<b>v</b> .	Io=10mA	, v,	111 1	5
	Δ		10-10IIIA	100		
Load	V <sub>OLOAD</sub> Conditio			180	mV	
Regulation	ns	V <sub>IN</sub> =	=14V, Io=0 t	to 1A		
	V <sub>DIF1</sub> Conditio			0.3		
Dropout	Conditio ns		Io=0.5A			407 42
Voltage	V <sub>DIF2</sub>			0.6	V	
Ü	Conditio		Io=1A			
Quiescent	ns		10-171	600		8 / 7
Circuit	Iq			000	μΑ	
Current	Conditio ns	$V_{IN}=1$	4V,Io=0A,V	$I_{\rm C}=2V$ ,	μΑ	
Circuit	T (0777)			1		41 >
Current at	Iq(OFF)			1	μΑ	
Output OFF	Conditio ns	V	$T_{\rm IN}=7V, V_{\rm C}=0$	ov 🔨	μА	
Temperature	∠Vo/					
Coefficient	∠Ta		±1.5			
of Output	Conditio	-	E' 0 . 100%		mV/°C	
Voltage	ns	]	Γj=0 to 100°		100	
Ripple			66			
Rejection	R <sub>REJ</sub> Conditio	37 1		10011	dB	
	ns		4V,f=100 to	120HZ		
Overcurrent	$I_{S1}$	1.1		-5	-	
Protection	Conditio				A	
Starting Current*2	ns		$V_{IN}=14V$			
Control						
Voltage (Output	V <sub>c</sub> ,IH	2.0				
ON)*3 Control					V	
Voltage (Output	V <sub>C</sub> ,IL			0.8		
V <sub>C</sub> OFF) Control	/			40		
al Current (Output	I <sub>C</sub> ,IH Conditio			40	-	
ON) Control	ns		$V_C=2V$		μΑ	
Current	I <sub>C</sub> ,IL	-5	0		, r.,	
(Output OFF)	Conditio ns		$V_C=0V$			
Input	V <sub>OVP</sub>	33				
Overvoltage Shutdown	Conditio		T 10		V	
Voltage	ns		Io=10mA			
dd D C	.1 1	C 1: (		•	1	1

<sup>\*1:</sup> Refer to the clause of a difference in input and output voltage.

<sup>\*2:</sup> Is1 is specified at the 5% drop point of output voltage Vo on the condition that VIN = overcurrent protection starting current, Io = 10mA.

<sup>\*3:</sup> Output is OFF when the output control terminal Vc is open. Each input level is equivalent to LS-TTL level. Therefore, the device can be driven directly by LS-TTLs.

### Attention ...

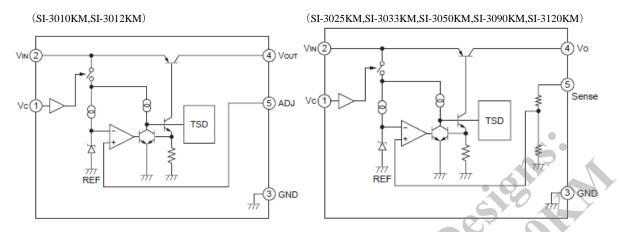
- SI-3120KM cannot be used in the following applications because the built-in foldback-type overcurrent protection may cause errors during start-up stage;
- (1) Constant current load (2) Positive and negative power supply (3) Series-connected power supply (4) Vo adjustment by raising ground voltage

As PD= $(VIN-Vo) \times Io$ , VIN(MAX) and Io(MAX) must be referred to the data of P17, copper area vs power dissipation upon actual applications.



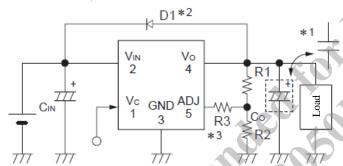
### • 2-3 Circuit Diagram

### 2-3-1 Block Diagram

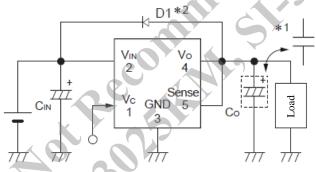


### 2-3-2 Typical Connection Diagram

(SI-3010KM,SI-3012KM)



(SI-3025KM,SI-3033KM,SI-3050KM,SI-3090KM,SI-3120KM)



### \*1 For SI-3012KM,SI-3025KM,SI-3033KM.

It is the setup to use a ultra-low ESR capacitor such as a ceramics-capacitor for Co with these models. When an electrolytic-capacitor is used for Co, they may oscillate at low-temperature.

\*1 For SI-3010KM,SI-3050KM,SI-3090KM,SI-3120KM.

As for these models, they may oscillate when a ultra-low ESR capacitor such as ceramic-capacitor is used for Co.

\*2: D1: Reverse biased protection diodes

In the case of reverse bias between input and output, this diode will be required.

(Recommended diodes: SJPL-H2 made by Sanken)

It is unnecessary in case of Vo≤3.3V.

R1, R2: resistors for setting output voltages

Output voltages can be adjusted by connecting R1 and R2 as shown in the above figure.

R2:  $10k\Omega$  is recommended.(In case of the SI-3120KM,24k $\Omega$  is recommended.)

 $R1 = (Vo-V_{ADJ}) / (V_{ADJ}/R2)$ 

Act Reconnected States of \*3: In the case that Vo  $\leq 1.5$ V is set, R3 should be inserted. 10k $\Omega$  is recommended for R3.

# 3. Operational Description

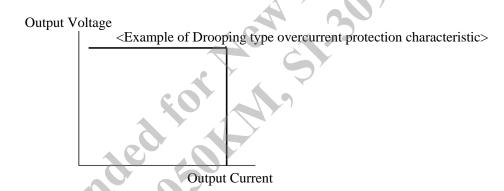
### • 3-1 Voltage Control

In the SI-3000KM series, the driving circuit is controlled by comparing the reference voltage with the ADJ terminal voltage (voltage divided by Vo detection resistor in fixed output products) to stabilize the output voltage by varying the voltage between the emitter and collector of a main PNP power transistor. The product of voltage between emitter and collector and the output current at this moment is consumed as heat.

### • 3-2 Overcurrent Protection

# 3-2-1 Overcurrent Protection Characterization for SI-3012KM,SI-3025KM,SI-3033KM

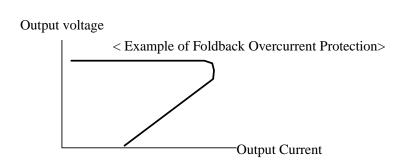
The Drooping type overcurrent protection function is provided in these models. In the case of the series regulator, as the output voltage drops subject to the overcurrent protection, the difference of input/output voltages increases to cause significant heating. Special care should be taken for the current limiting type overcurrent protection, since large current flows continuously.



# 3-2-2 Overcurrent Protection Characterization for SI-3010KM,SI-3050KM,SI-3090KM,SI-3120KM

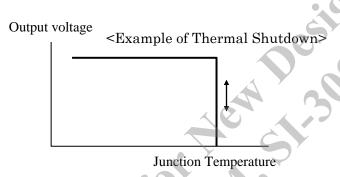
The foldback type overcurrent protection function is provided in these models. After operation of the overcurrent protection function, if the load resistance decreases and the output voltage drops, the output current of products is squeezed to reduce the increase of loss. However, in the case of the foldback type overcurrent protection function, since current limiting is also made at start-up, the function may not be used for the following applications, as it may cause a start-up error.

- (1) Constant current loads
- (2) Plus/minus power supply
- (3) DC power supply
- (4) Output voltage adjustment by grounding-up



### • 3-3 Thermal Shutdown

This IC is provided with the overheat protection circuit which detects the semiconductor junction temperature of the IC to limit the driving current, when the junction temperature exceeds the set value (around  $150^{\circ}$ C). Since the minimum operating temperature of the overheat protection circuit is  $130^{\circ}$ C, the thermal design of Tj <125 °C is required. Since the overheat protection has no hysteresis, as soon as the overload state is released and Tj falls below the set temperature, the normal operation is automatically restored. When the overheat protection function is operated in the overload state, the output voltage falls, but at the same time the output current is decreased and in the consequence, overheat protection operation and automatic restoration are repeated in a short interval, resulting eventually in the waveforms of output voltage oscillation.



\*Note for thermal shutdown characteristic

This circuit protects the IC against overheat resulting from the instantaneous short circuit, but it should be noted that this function does not assure the operation including reliability in the state that overheat continues due to long time short circuit.

### 4. Cautions

### • 4-1 External Components

### 4-1-1 Input Capacitor CIN

The input capacitor is required to eliminate noise and stabilize the operation and values of  $0.47\mu F$  -  $22\mu F$  are recommended. Any of ceramic capacitors or electrolytic ones may be used for the input capacitor.

### 4-1-2 Output Capacitor Co

Co for SI-3010KM,SI-3050KM,SI-3090KM,SI-3120KM

In the output capacitor Co, larger capacitance than the recommended value is required for phase compensation. Equivalent series resistance values (ESR) of capacitors are limited, and depending on products, therefore the type of recommended capacitors is limited.

Recommended ESR values for SI-3010KM,SI-3050KM,SI-3090KM,SI-3120KM:  $2\Omega > \text{ESR} > 0.2\Omega$  It is recommended to use electrolytic capacitors. When capacitors with ultra-low ESR such as ceramic capacitors, functional polymer capacitors,OS-capacitors etc., are used, phase margin is decreased, possibly causing the oscillation of output voltage. Therefore these capacitors can not be used.

### Co for SI-3012KM, SI-3025KM, SI-3033KM

Using a ceramics capacitor and a function polymer capacitor, OS-capacitor etc., is recommended.

As for these models, when a big-ESR capacitor such as electrolytic-capacitors was used, phase margin is decreased and possibly causing the oscillation of output voltage. ESR's increase in the low temperature condition. Therefore,

an electrolytic-capacitor can't be recommended because output may oscillate at a low temperature even when the output doesn't oscillate at a room temperature.

### 4-1-3 Reverse bias protection diode D1

In the case of falling-down of the input voltage, it is recommended to insert a protection diode D1 against the reverse bias between input and output. However, in the case of setting the Vout < 3.3V or lower, D1 is not required including the case of reverse bias. In order to select a suitable D1, it should be taken into consideration that the diode has adequate forward current withstand voltage against the instantaneous discharge of energy stored in output capacitor Co.

The permissible value of the forward current per unit time of diode is specified in  $I_{FSM}$  (A) and in the case of our diode, it is specified at 50Hz half wave (10ms), but it should be noted that different companies may specify different times. The selection of diode should be made by converting the specified time into the actual discharging time so as to meet the required  $I_{FSM}$  (A). The discharging time of Co is normally shorter than 1ms, but it is recommended to do the conversion with 1ms in consideration of margin.

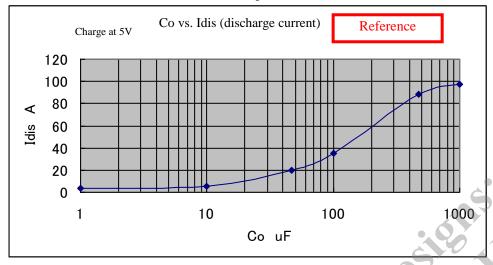
For conversion into  $I_{FSM}$ , calculation should be made by using the equations (1) and (2).

$$\left(\frac{I_{FSM}}{\sqrt{2}}\right)^2 * t1 = X$$
 --- (1) As for  $I_{FSM}$ , please refer to the catalog of each company.

t1 = specified time in catalog of each company

Converted IFSM = 
$$\sqrt{\frac{2*X}{t^2}}$$
 --- (2) t2: converted time (discharging time of Co)

<Graph 1>



On the assumption of Cout =  $470\mu F$ ,  $I_{FSM}$  of around 90A or more (in 1ms time period) is required and according to our specifications of diode,  $I_{FSM}$  is specified for 10ms, therefore the diode of 30A has the tolerated dose of 94.8A (in 1ms) to prove that it is usable.

### • 4-2 Pattern Design Notes

### 4-2-1 Input / Output Capacitor

The input capacitor C1 and the output capacitor C2 should be connected to the IC as close as possible. If the rectifying capacitor for AC rectifier circuit is on the input side, it can be used as an input capacitor. However, if it is no close to the IC, the input capacitor should be connected in addition to the rectifying capacitor.

### 4-2-2 ADJ Terminal (Output Voltage Set-up for SI-3010KM & SI-3012KM)

The ADJ terminal is a feedback detection terminal for controlling the output voltage. The output voltage set-up is achieved by connecting R1 and R2.

SI-3010KM: it should be set in a manner that  $I_{ADJ}$  is around 100 $\mu$ A.

SI-3012KM: it should be set in a manner that I<sub>ADJ</sub> is around 50μA.

### R1, R2 and output voltage can be obtained by the following equations:

$$R1 = (Vo-V_{ADJ}) / I_{ADJ}$$
 
$$R2 = V_{ADJ} / I_{ADJ}$$
 
$$Vout = R1 \times (V_{ADJ} / R2) + V_{ADJ}$$

## 5. Applications

### • 5-1 Output ON / OFF Control

The ON/OFF control of output can be made by directly applying voltage to No. 1 Vc terminal. When the Vc terminal is open, the operation is in OFF. The Vc terminal is in OFF below 0.8V and in ON at above 2V.

### • 5-2 Thermal Design

### 5-2-1 Calculation of heat dissipation

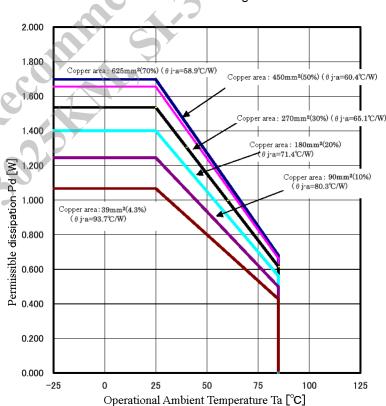
Heat generation of the surface mounting IC is generally dependent on size, material and copper foil area of the mounted printed circuit board. Full attention should be paid to heat dissipation and adequate margin be taken into consideration at thermal design. In order to enhance the heat dissipation effect, it is recommended to enlarge the copper foil area connected to the stem part on the back side of the product. The copper foil area of the printed circuit board significantly affects the heat dissipation effect.

As the junction temperature Tj (MAX) is an inherent value, it must be observed strictly. For this purpose, heat sink design (thermal resistance of board) which is appropriate for Pd (MAX) and Ta MAX is required. This is graphically shown in the heat derating curve for easy understanding. The heat dissipation design is done in the following procedure.

- 1) The maximum ambient temperature in the set Ta MAX is obtained.
- 2) The maximum loss PdMAX which varies the input/output conditions is obtained.

 $Pd = (V_{IN} - V_{Out}) \times I_{Out}$ 

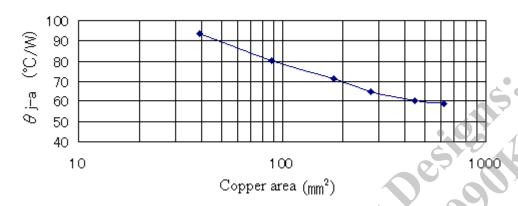
3) The area of copper foil is determined from the intersection point in the heat derating curve below shown.

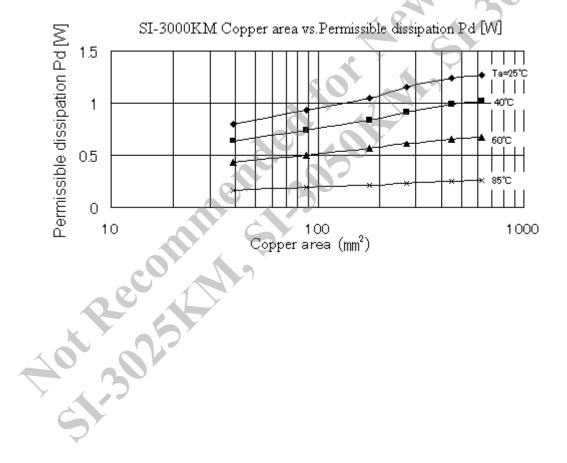


SI-3000KM series derating curve

For reference information, the graph of copper foil area vs. thermal resistance between junction temperature and ambient temperature  $\theta$ j-a and the graph of copper foil area vs. permissible dissipation that both are in the single side copper foil board FR - 4 are shown below.

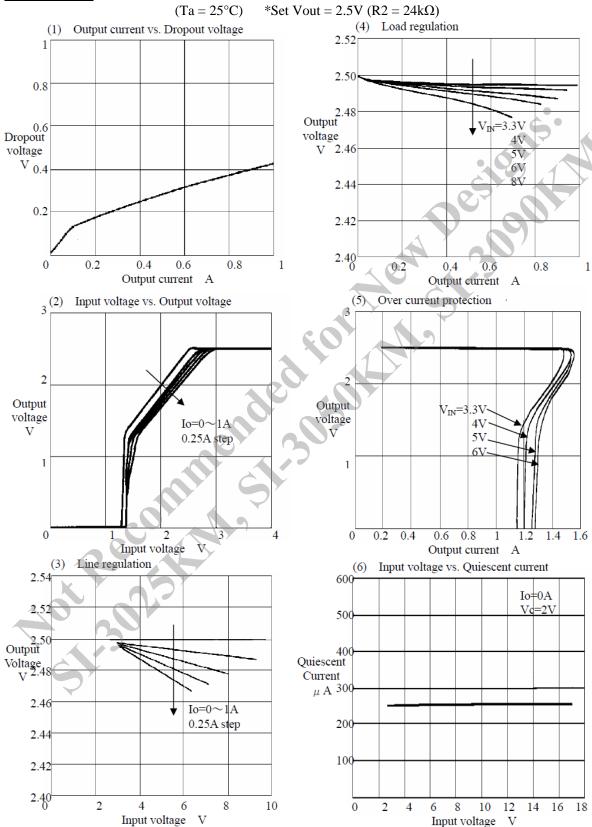
SI-3000KM Copper area vs. Thermal Resistance

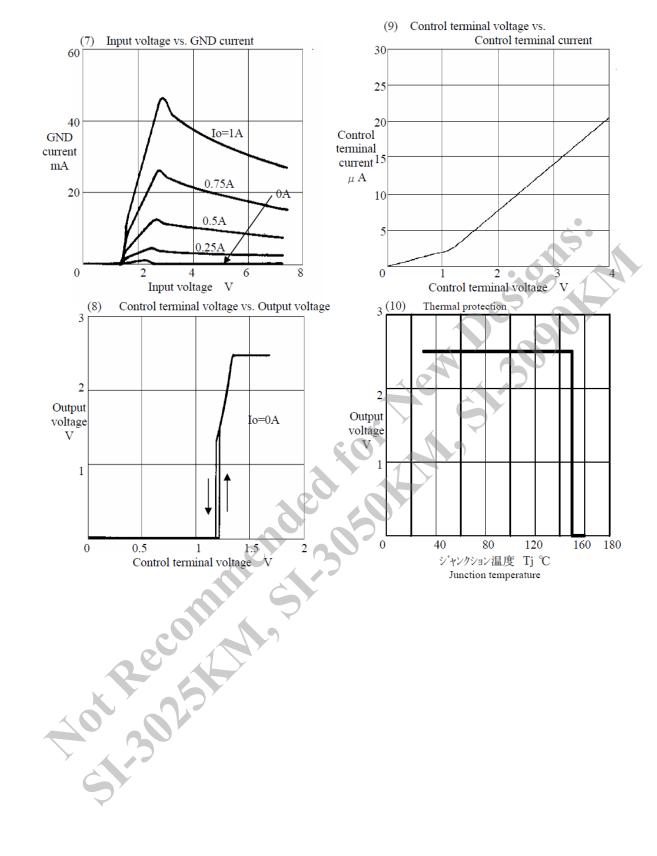




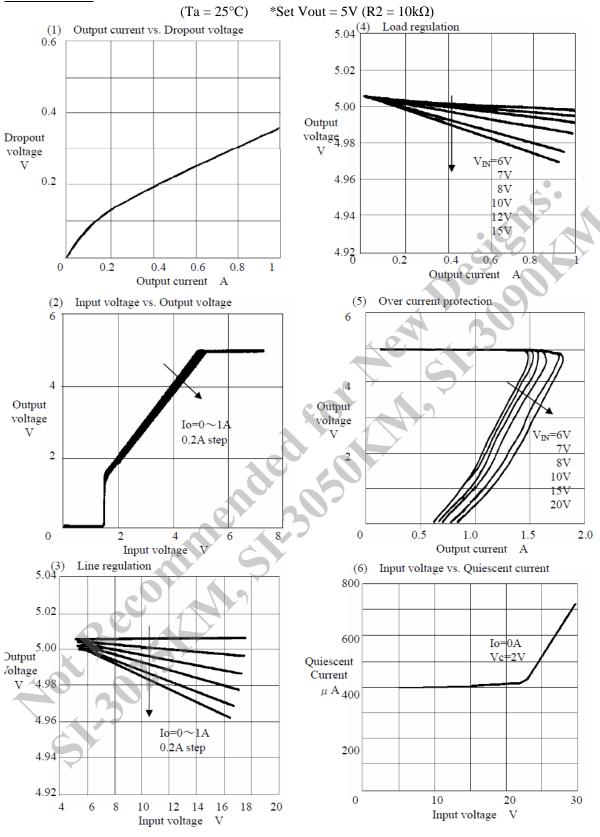
# 6. Typical Characteristics

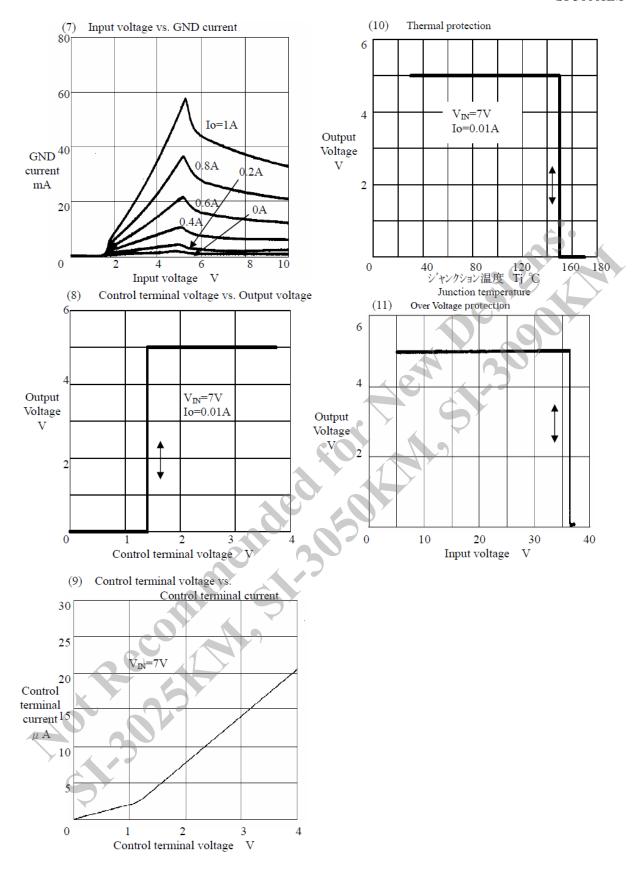
### 6.1 SI-3012KM





### 6.1 SI-3010KM





### Notice

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